

NTB6410AN, NTP6410AN, NVB6410AN

N-Channel Power MOSFET 100 V, 76 A, 13 mΩ

Features

- Low $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ Unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	
Power Dissipation $R_{\theta JC}$	P_D	$T_C = 25^\circ\text{C}$	W
Pulsed Drain Current	I_{DM}	305	A
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to $+175$	$^\circ\text{C}$
Source Current (Body Diode)	I_S	76	A
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 50$ Vdc, $V_{GS} = 10$ Vdc, $I_{L(pk)} = 57.7$ A, $L = 0.3$ mH, $R_G = 25$ Ω)	E_{AS}	500	mJ
Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds	T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) Steady State	$R_{\theta JC}$	0.8	$^\circ\text{C/W}$
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	32	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

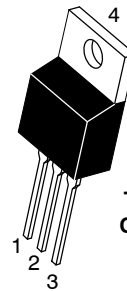
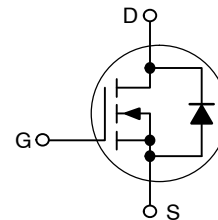


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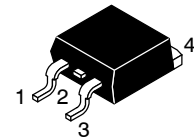
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$ (Note 1)
100 V	13 mΩ @ 10 V	76 A

N-Channel

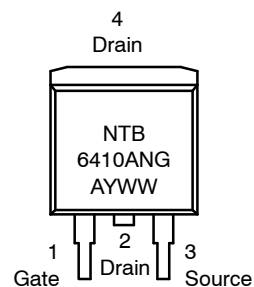
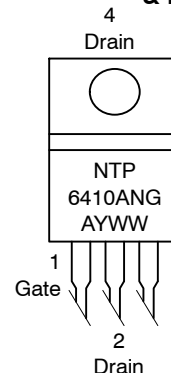


TO-220AB
CASE 221A
STYLE 5



D2PAK
CASE 418B
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENT



6410AN = Specific Device Code
G = Pb-Free Device
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C Unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			94		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 100 V	T _J = 25°C		1.0	μA
			T _J = 150°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250 μA	2.0		4.0	V
Negative Threshold Temperature Coefficient	V _{GS(th)} /T _J			9.0		mV/°C
Drain-to-Source On-Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 76 A		11	13	mΩ
		V _{GS} = 10 V, I _D = 20 A		10	12	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 20 A		40		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		4500		pF
Output Capacitance	C _{oss}			650		
Reverse Transfer Capacitance	C _{rss}			250		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 80 V, I _D = 76 A		120		nC
Threshold Gate Charge	Q _{G(TH)}			5.2		
Gate-to-Source Charge	Q _{GS}			20		
Gate-to-Drain Charge	Q _{GD}			57		
Plateau Voltage	V _{GP}			5.1		V
Gate Resistance	R _G			2.4		Ω

SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DD} = 80 V, I _D = 76 A, R _G = 6.2 Ω		17		ns
Rise Time	t _r			170		
Turn-Off Delay Time	t _{d(off)}			120		
Fall Time	t _f			190		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	I _S = 76 A	T _J = 25°C		1.0	1.3	V
			T _J = 125°C		0.9		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, I _S = 76 A, di _{SD} /dt = 100 A/μs		93			ns
Charge Time	t _a			69			
Discharge Time	t _b			24			
Reverse Recovery Charge	Q _{RR}			300			nC

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

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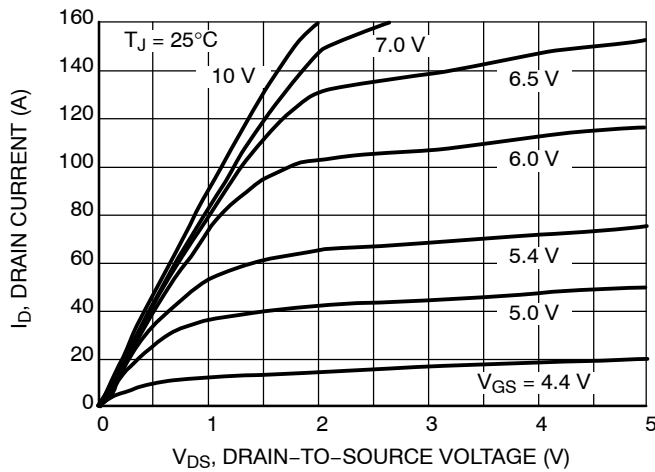


Figure 1. On-Region Characteristics

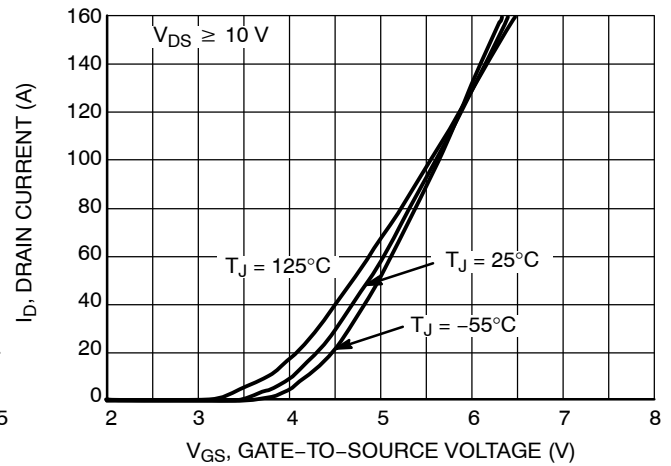


Figure 2. Transfer Characteristics

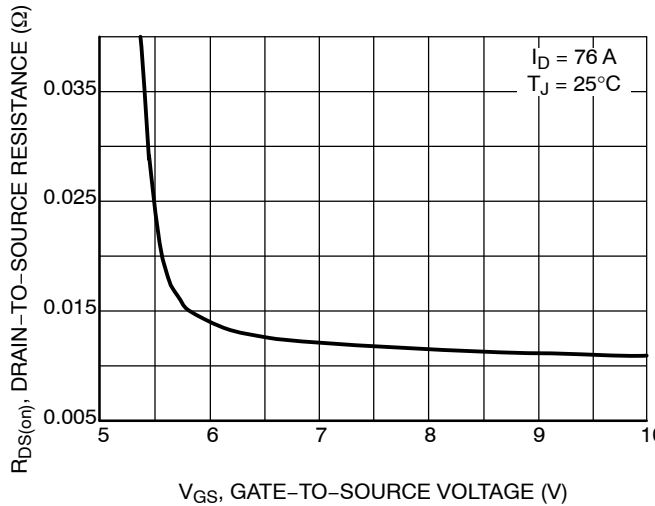


Figure 3. On-Region versus Gate Voltage

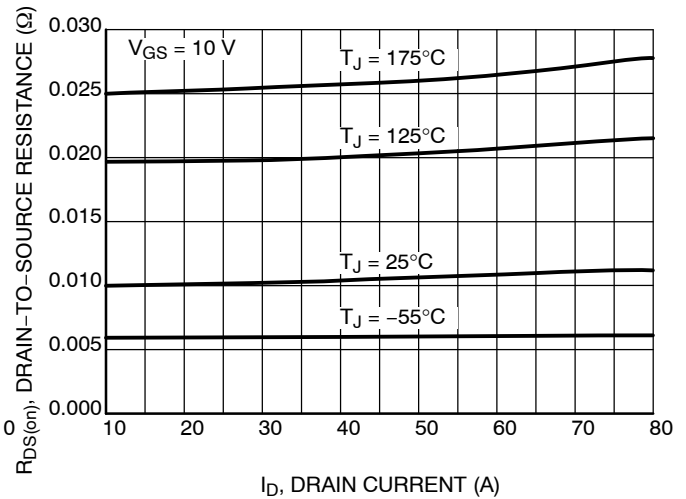


Figure 4. On-Region versus Drain Current and Gate Voltage

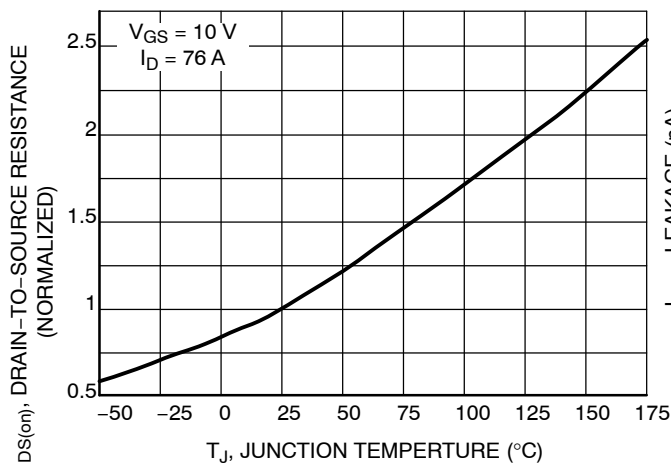


Figure 5. On-Resistance Variation with Temperature

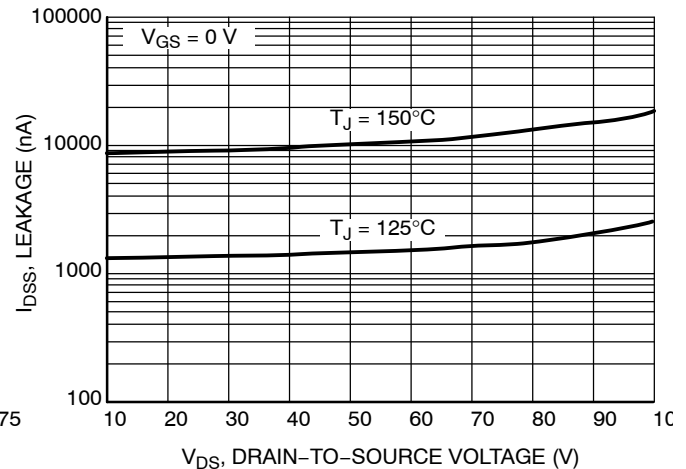


Figure 6. Drain-to-Source Leakage Current versus Voltage

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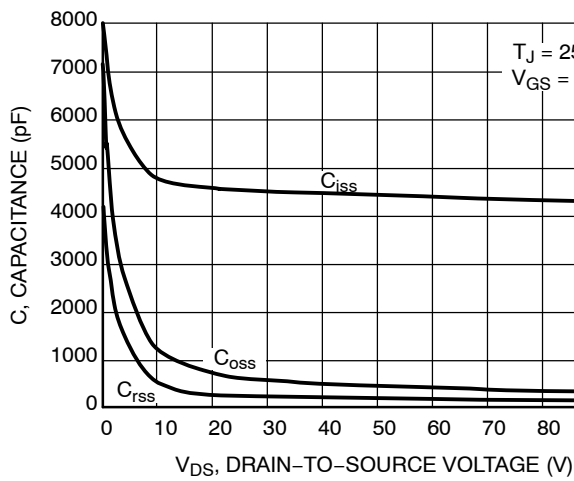


Figure 7. Capacitance Variation

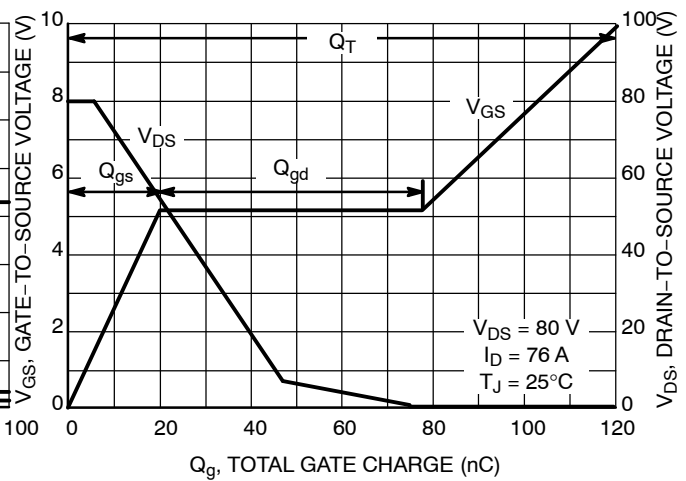


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

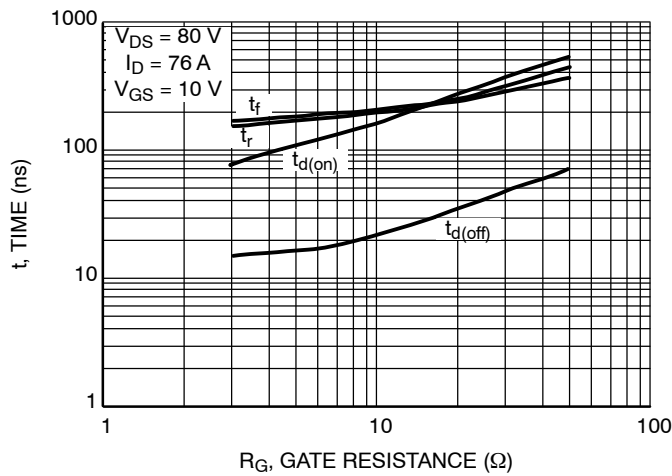


Figure 9. Resistive Switching Time Variation versus Gate Resistance

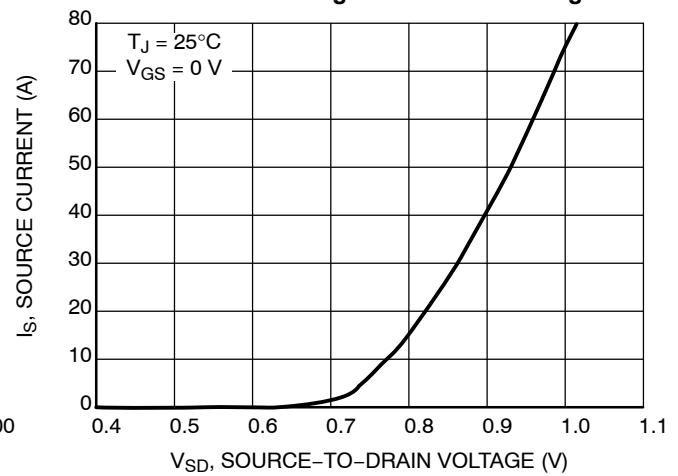


Figure 10. Diode Forward Voltage versus Current

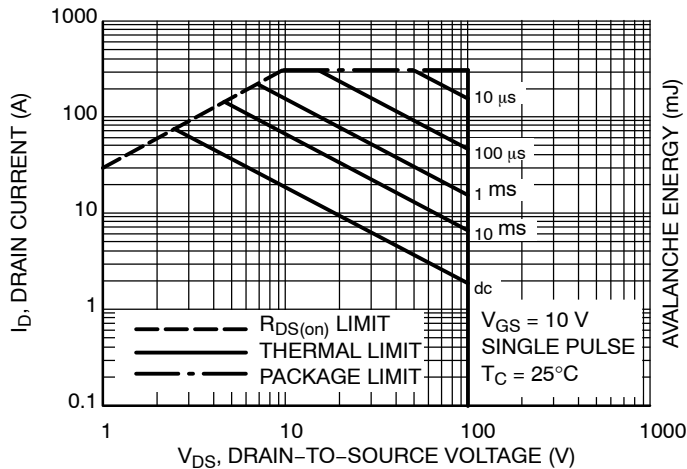


Figure 11. Maximum Rated Forward Biased Safe Operating Area

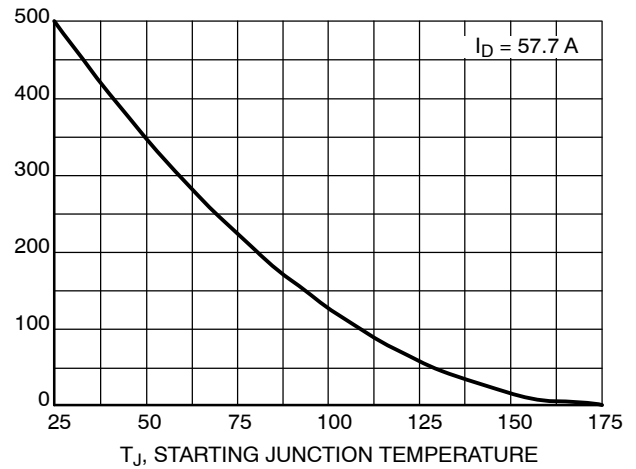


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

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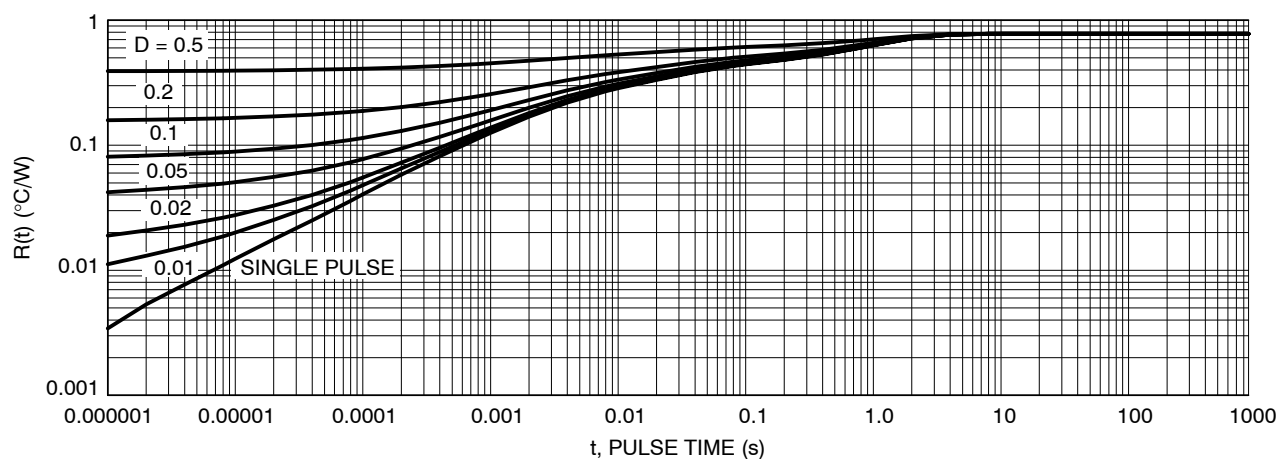


Figure 13. Thermal Response

ORDERING INFORMATION

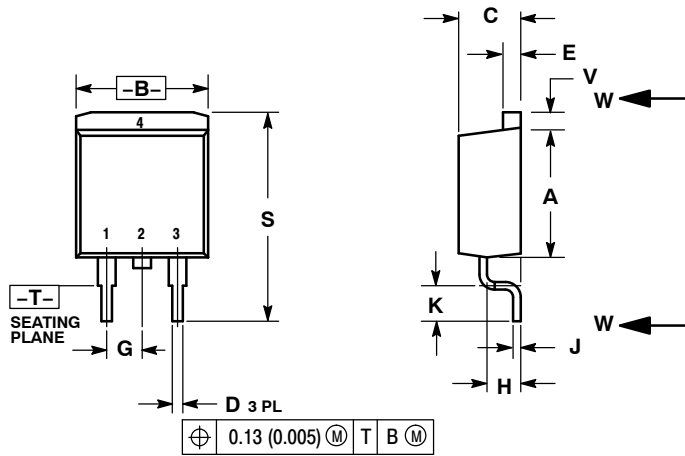
Device	Package	Shipping [†]
NTB6410ANG	D ² PAK (Pb-Free)	50 Units / Rail
NTB6410ANT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NTP6410ANG	TO-220 (Pb-Free)	50 Units / Rail
NVB6410ANT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTB6410AN, NTP6410AN, NVB6410AN

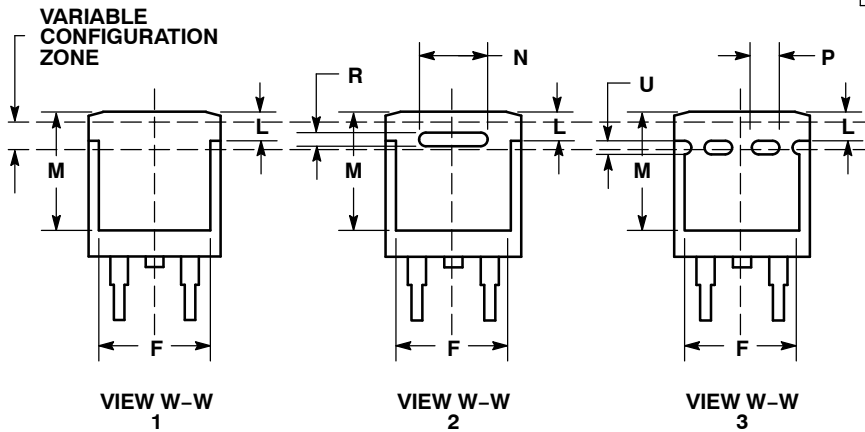
PACKAGE DIMENSIONS

D²PAK 3 CASE 418B-04 ISSUE K



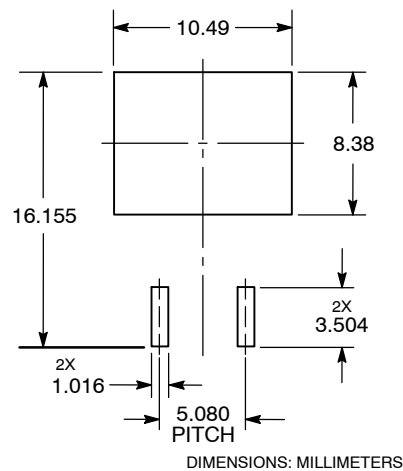
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



- STYLE 2:
- PIN 1. GATE
 - DRAIN
 - SOURCE
 - DRAIN

SOLDERING FOOTPRINT*

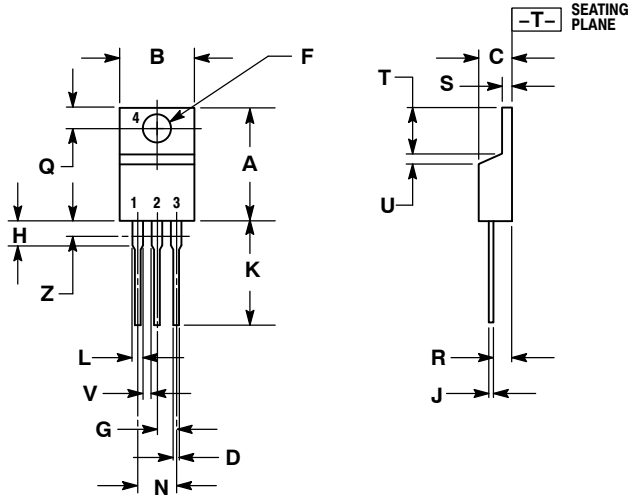


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AG



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 4:

- PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

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NTB6410AN/D



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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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